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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	36
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 10x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f410cbt3

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3.4 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

3.5 Embedded Flash memory

The devices embed up to 128 Kbytes of Flash memory available for storing programs and data, plus 512 bytes of OTP memory organized in 16 blocks which can be independently locked.

To optimize the power consumption the Flash memory can also be switched off in Run or in Sleep mode (see Section 3.18: Low-power modes).

Two modes are available: Flash in Stop mode or in DeepSleep mode (trade off between power saving and startup time.

Before disabling the Flash, the code must be executed from the internal RAM.

3.6 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.7 Embedded SRAM

All devices embed 32 Kbytes of system SRAM which can be accessed (read/write) at CPU clock speed with 0 wait states

Functional overview STM32F410x8/B

3.8 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs) and the slaves (Flash memory, RAM, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

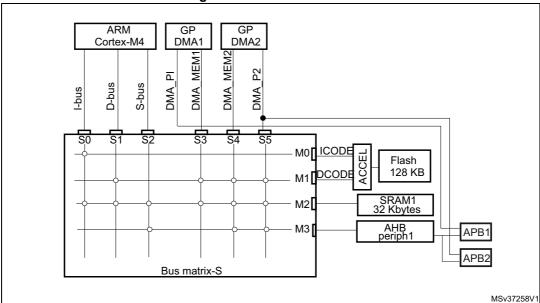


Figure 3. Multi-AHB matrix

3.9 DMA controller (DMA)

The devices feature two general-purpose dual-port DMAs (DMA1 and DMA2) with 8 streams each. They are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. They feature dedicated FIFOs for APB/AHB peripherals, support burst transfer and are designed to provide the maximum peripheral bandwidth (AHB/APB).

The two DMA controllers support circular buffer management, so that no specific code is needed when the controller reaches the end of the buffer. The two DMA controllers also have a double buffering feature, which automates the use and switching of two memory buffers without requiring any special code.

Each stream is connected to dedicated hardware DMA requests, with support for software trigger on each stream. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals:

- SPI and I²S
- I²C
- USART
- General-purpose, basic and advanced-control timers TIMx
- ADC
- DAC.

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3.17 Real-time clock (RTC) and backup registers

The backup domain includes:

- The real-time clock (RTC)
- 20 backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the second, minute, hour (in 12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are performed automatically. The RTC features a reference clock detection, a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision. The RTC provides a programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes. The sub-seconds value is also available in binary format.

It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-speed RC has a typical frequency of 32 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural quartz deviation.

Two alarm registers are used to generate an alarm at a specific time and calendar fields can be independently masked for alarm comparison. To generate a periodic interrupt, a 16-bit programmable binary auto-reload downcounter with programmable resolution is available and allows automatic wakeup and periodic alarms from every 120 µs to every 36 hours.

A 20-bit prescaler is used for the time base clock. It is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see Section 3.18: Low-power modes).

Additional 32-bit registers contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

The RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the V_{BAT} pin.

3.18 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

To further reduce the power consumption, the Flash memory can be switched off before entering in Sleep mode. Note that this requires a code execution from the RAM.

Stop mode

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC

Pinouts and pin description

Table 10.	Alternate	function	mapping	(continued)

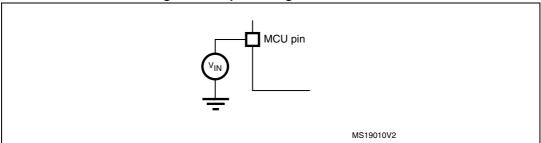
		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
Po	ort	SYS_AF	TIM1/LPTIM1	TIM5	TIM9/ TIM11	I2C1/I2C2 /I2C4	SPI1/I2S1/S PI2/I2S2	SPI1/I2S1/ SPI2/I2S2/ SPI5/I2S5	USART1/ USART2	USART6	12C2/ 12C4	-	-	-		1	SYS_AF
	PB0	-	TIM1_CH2N	-	-	-	-	SPI5_SCK/ I2S5_CK	-	-	-	-	-	-	-	-	EVENTOUT
	PB1	-	TIM1_CH3N	-	-	-	-	SPI5_NSS/ I2S5_WS	-	-	-	-	-	-	-	-	EVENTOUT
	PB2	-	LPTIM1_OUT	-	-	=	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PB3	JTDO- SWO	-	-	-	I2C4_ SDA	SPI1_SCK/I 2S1_CK	-	USART1_ RX	-	I2C2_ SDA	-	-	-	-	-	EVENTOUT
	PB4	JTRST	-	-	ı	-	SPI1_MISO	-	1	-	1	-	-	-	-	1	EVENTOUT
	PB5	-	LPTIM1_IN1	-	-	I2C1_ SMBA	SPI1_MOSI /I2S1_SD	-	-	-	-	-	-	-	-	-	EVENTOUT
	PB6	-	LPTIM1_ETR	-	-	I2C1_ SCL	-	-	USART1_ TX	-	-	-	-	-	-	-	EVENTOUT
	PB7	-	LPTIM1_IN2	-	-	I2C1_ SDA	-	-	USART1_ RX	-	-	-	-	-	-	-	EVENTOUT
Port B	PB8	-	LPTIM1_OUT	-	-	I2C1_ SCL	-	SPI5_MOSI /I2S5_SD	-	-	-	-	-	-	-	-	EVENTOUT
	PB9	-	-	-	TIM11_ CH1	I2C1_ SDA	SPI2_NSS/ I2S2_WS	-	-	-	I2C2_ SDA	-	-	-	-	-	EVENTOUT
	PB10	-	-	-	-	I2C2_ SCL	SPI2_SCK/ I2S2_CK	I2S1_MCK	-	-	I2C4_ SCL	-	-	-	-	-	EVENTOUT
	PB11	TRACED3	1	TIM5_ CH4	ı	I2C2_ SDA	I2S2_CKIN	ı	ı	-	ı	-	-	-	ı	i	EVENTOUT
	PB12	-	TIM1_BKIN	TIM5_ CH1	-	I2C2_ SMBA	SPI2_NSS/ I2S2_WS	-	-	-	-	-	-	-	-	-	EVENTOUT
	PB13	-	TIM1_CH1N	-	ı	I2C4_ SMBA	SPI2_SCK /I2S2_CK	-	-	-	ı	-	-	-	ı	ı	EVENTOUT
	PB14	-	TIM1_CH2N	-	-	I2C4_ SDA	SPI2_MISO	-	-	-	ı	-	-	-	-	-	EVENTOUT
	PB15	RTC_ 50Hz	TIM1_CH3N	-	-	I2C4_ SCL	SPI2_MOSI /I2S2_SD	-	-	-	-	-	-	-	-	-	EVENTOUT



6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 12*.

Figure 12. Input voltage measurement



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{RUSH} ⁽²⁾	In-Rush current on voltage regulator power- on (POR or wakeup from Standby)	-	-	160	200	mA
E _{RUSH} ⁽²⁾	In-Rush energy on voltage regulator power- on (POR or wakeup from Standby)	V _{DD} = 1.7 V, T _A = 125 °C, I _{RUSH} = 171 mA for 31 μs	-	-	5.4	μC

Table 20. Embedded reset and power control block characteristics (continued)

- The product behavior is guaranteed by design down to the minimum V_{POR/PDR} value.
- 2. Guaranteed by design.
- 3. The reset timing is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is fetched by the user application code.

6.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 14: Current consumption measurement scheme*.

All the run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at VDD or VSS (no load).
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted to both f_{HCLK} frequency and VDD ranges (refer to *Table 16: Features depending on the operating power supply range*).
- The voltage scaling is adjusted to f_{HCLK} frequency as follows:
 - Scale 3 for f_{HCLK} ≤ 64 MHz
 - Scale 2 for 64 MHz < f_{HCLK} ≤ 84 MHz
 - Scale 1 for 84 MHz < f_{HCLK} ≤ 100 MHz
- The system clock is HCLK, f_{PCLK1} = f_{HCLK}/2, and f_{PCLK2} = f_{HCLK}.
- External clock is 4 MHz and PLL is ON except if it is explicitly mentioned.
- The maximum values are obtained for V_{DD} = 3.6 V and a maximum ambient temperature (T_A), and the typical values for T_A= 25 °C and V_{DD} = 3.3 V unless otherwise specified.

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Table 25. Typical and maximum current consumption in run mode, code with data processing (ART accelerator disabled) running from Flash memory - V_{DD} = 3.6 V

				Voltage	PLL VCO	Тур		Ma	x ⁽²⁾		
Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Voltage scale	(MHz) (1)	T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	T _A = 125 °C	Unit
			100	S1	200	24.7	26.3	26.5	27.0	28.0	
			84	S2	168	21.6	23.0	23.2	23.7	24.7	
		External clock, all peripherals	64	S3	128	15.9	17.0	17.1	17.6	18.6	
		enabled ⁽³⁾⁽⁴⁾	50	S3	100	13.1	14.2	14.3	14.7	15.7	
			25	S3	100	7.5	8.2	8.3	8.7	9.7	
	Supply current in		20	S3	160	6.5	7.1	7.2	7.5	8.5	
		HSI, PLL OFF, all peripherals enabled ⁽³⁾⁽⁴⁾	16	S3	off	4.7	5.3	5.5	5.9	6.9	
I _{DD}			1	S3	off	0.8	1.2	1.6	1.9	2.9	mΔ
טטי	Run mode		100	S1	200	19.1	20.5	20.7	21.3	22.3	1117 (
			84	S2	168	17.1	18.3	18.6	19.1	20.1	
		External clock, all peripherals	64	S3	128	12.8	13.8	14.0	14.5	15.5	
		disabled ⁽³⁾	50	S3	100	10.7	11.7	11.8	12.2	13.2	
			25	S3	100	6.3	7.0	7.1	7.4	8.3	
			20	S3	160	5.4	6.0	6.2	6.5	7.4	
		HSI, PLL OFF,	16	S3	off	4.0	4.5	5.0	5.1	6.0	
		all peripherals disabled ⁽³⁾	1	S3	off	0.8	1.1	1.5	1.8	2.7	

^{1.} Refer to Table 44 and RM0401 for the possible PLL VCO setting

^{2.} Guaranteed by characterization, unless otherwise specified.

^{3.} When the ADC is ON (ADON bit set in ADC_CR2), an additional power consumption of 1.6 mA must be added.

^{4.} Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register)

Table 26. Typical and maximum current consumption in run mode, code with data processing (ART accelerator disabled) running from Flash memory - V_{DD} = 1.7 V

			£	Voltago	PLL VCO	Тур		Ma	ax ⁽²⁾		
Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Voltage scale	(MHz) (1)	T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	T _A = 125 °C	Unit
			100	S1	200	24.2	26.2	25.7	26.5	27.6	
			84	S2	168	20.0	21.8	21.4	22.1	23.1	
		External clock, all peripherals	64	S3	128	15.8	17.2	17.0	17.7	18.7	
		enabled ⁽³⁾⁽⁴⁾	50	S3	100	13.3	16.5	14.4	15.0	16.0	
			25	S3	100	7.5	9.5	8.3	8.8	9.8	
	Supply current in		20	S3	160	6.7	8.2	7.3	7.7	8.6	
		HSI, PLL OFF, all peripherals enabled ⁽³⁾⁽⁴⁾	16	S3	off	5.1	6.4	5.7	6.2	7.1	
			1	S3	off	0.8	1.0	1.3	1.7	2.6	mA
I _{DD}	Run mode		100	S1	200	18.6	23.0	23.4	23.9	24.9	IIIA
			84	S2	168	15.5	19.3	19.9	20.4	21.4	
		External clock, all peripherals	64	S3	128	12.7	16.1	16.7	17.0	18.0	
		disabled ⁽³⁾	50	S3	100	10.9	13.9	14.3	14.7	15.7	
			25	S3	100	6.3	8.1	8.4	8.7	9.7	
			20	S3	160	5.6	7.2	7.3	7.6	8.4	
		HSI, PLL OFF,	16	S3	off	4.3	5.5	5.8	6.2	7.1	
		all peripherals disabled ⁽³⁾	1	S3	off	0.8	1.0	1.3	1.6	2.5	

^{1.} Refer to Table 44 and RM0401 for the possible PLL VCO setting

^{2.} Guaranteed by characterization, unless otherwise specified.

^{3.} When the ADC is ON (ADON bit set in ADC_CR2), an additional power consumption of 1.6 mA must be added.

^{4.} Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register)

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- The ART accelerator is ON.
- Voltage Scale 2 mode selected, internal digital voltage V12 = 1.26 V.
- HCLK is the system clock at 100 MHz. f_{PCLK1} = f_{HCLK}/2, and f_{PCLK2} = f_{HCLK}.
 The given value is calculated by measuring the difference of current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on
- Ambient operating temperature is 25 °C and V_{DD}=3.3 V.

Table 36. Peripheral current consumption

Perip	pheral	Voltage scale1	Voltage scale2	Voltage scale3	Unit
	GPIOA	1.68	1.62	1.42	
	GPIOB	1.67	1.60	1.41	
	GPIOC	1.63	1.56	1.39	
	GPIOH	0.61	0.61	0.52	
AHB1	CRC	0.31	0.32	0.25	μΑ/MHz
(up to 100 MHz)	DMA1 ⁽¹⁾	1.67N + 3.12	1.60N + 2.96	1.43N + 2.64	-
	DMA2 ⁽¹⁾	1.59N + 2.83	1.52N + 2.65	1.36N + 2.41	
	RNG	0.90	0.88	0.75	
	APB1 to AHB	0,78	0,74	0,63	
	TIM5	13,38	12,76	11,41	
	TIM6	2,14	1,98	1,75	
	LPTIM	8,22	7,88	7,06	
	WWDG	0,64	0,64	0,56	
APB1	SPI2/I2S2	2,42	2,33	2,06	
(up to 50 MHz)	USART2	3,38	3,29	2,91	μΑ/MHz
	I2C1	3,46	3,33	2,97	
	I2C2	3,50	3,31	2,97	
	I2C4	4,82	4,64	4,09]
	PWR	0,66	0,64	0,62	
	DAC	0,84	0,81	0,78	

Table 36. Peripheral current consumption (continued)

			I _{DD} (Typ)		
Perip	heral	Voltage scale1	Voltage scale2	Voltage scale3	Unit
	APB2 to AHB	0,22	0,19	0,17	
	TIM1	6,62	6,36	5,66	
	USART1	3,19	3,10	2,77	
	USART6	3,10	2,99	2,66	
4.550	ADC1	3,35	3,25	2,88	
APB2 (up to 100 MHz)	SPI1/I2S1	1,82	1,77	1,58	A /N/ILI-
(up to 100 WH12)	SYSCFG	0,83	0,81	0,72	μΑ/MHz
	EXTI	0,92	0,88	0,80	=
	TIM9	2,90	2,81	2,48	=
	TIM11	2,13	2,06	1,81	
	SPI5/I2S5	1,88	1,83	1,59	
Bus r	natrix	1.91	1.82	1.64	

^{1.} Valid if all the DMA streams are activated (please refer to the reference manual RM0401).

6.3.7 Wakeup time from low-power modes

The wakeup times given in Table 37 are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep modes: the wakeup event is WFE.
- WKUP (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

Wakeup from Stop mode, Option bytes are not reloaded main regulator CPU restart Regulator HSI restart Flash stop exit ramp-up Wakeup from Stop mode, Option bytes are not reloaded main regulator, flash in Deep power down mode HSI restart Flash Deep Pd recovery Regulator ramp-up Wakeup from Stop, Option bytes are not reloaded regulator in low power mode CPU restart Regulator HSI restart Flash stop exit ramp-up Wakeup from Stop, regulator in low power mode, Option bytes are not reloaded flash in Deep power down mode Flash Deep Pd recovery HSI restart Regulator ramp-up Wakeup from Standby mode Regulator OFF CPU restart Flash Deep Pd recovery Option bytes loading HSI restart Regulator restart Wakeup from Sleep and Regulator Option bytes are not reloaded Flash in Deep power down ON CPU restart Flash Deep Pd recovery

Figure 18. Low-power mode wakeup

All timings are derived from tests performed under ambient temperature and V_{DD} =3.3 V.

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The LSE high-power mode allows to cover a wider range of possible crystals but with a cost of higher power consumption.

		(LSE OF IN EACH OF IN										
Symbol	Parameter	Conditions	Min	Тур	Max	Unit						
R _F	Feedback resistor	-	-	18.4	-	MΩ						
I _{DD}	LSE current consumption	Low-power mode (default)	-	-	1	μΑ						
		High-drive mode	-	-	3							
G _m _crit_max	Maximum critical crystal a	Startup, low-power mode	-	-	0.56	μΑ/V						
	Maximum critical crystal g _m	Startup, high-drive mode	-	-	1.50	μΑVV						
t _{SU(LSE)} ⁽²⁾	startup time	V _{DD} is stabilized	-	2	-	s						

Table 41. LSE oscillator characteristics ($f_{LSE} = 32.768 \text{ kHz}$) (1)

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

For information about the LSE high-power mode, refer to the reference manual RM0401.

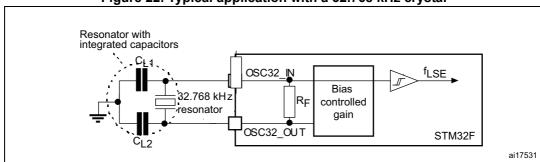


Figure 22. Typical application with a 32.768 kHz crystal

^{1.} Guaranteed by design.

t_{SU/LSE} is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is guaranteed by characterization. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

FMPI²C characteristics

The FMPI2C characteristics are described in Table 63.

Refer also to *Section 6.3.16: I/O port characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

Table 63. FMPI²C characteristics⁽¹⁾

	Parameter	Standard mode		Fast	mode	Fast+ mode		Unit
-		Min	Max	Min	Max	Min	Max	Unit
f _{FMPI2CC}	F _{MPI2CCLK} frequency	2	-	8	-	17 16 ⁽²⁾	-	
t _{w(SCLL)}	SCL clock low time	4.7	-	1.3	-	0.5	-	
t _{w(SCLH)}	SCL clock high time	4.0	-	0.6	-	0.26	-	
t _{su(SDA)}	SDA setup time	0.25	-	0.10	-	0.05	-	
t _{H(SDA)}	SDA data hold time	0	-	0	-	0	-	
t _{v(SDA,ACK)}	Data, ACK valid time	-	3.45	-	0.9	-	0.45	
$t_{r(SDA)} \ t_{r(SCL)}$	SDA and SCL rise time	-	0.100	-	0.30	-	0.12	
$t_{f(SDA)} \ t_{f(SCL)}$	SDA and SCL fall time	-	0.30	-	0.30	-	0.12	us
t _{h(STA)}	Start condition hold time	4	-	0.6	-	0.26	-	
t _{su(STA)}	Repeated Start condition setup time	4.7	-	0.6	-	0.26	-	
t _{su(STO)}	Stop condition setup time	4	-	0.6	-	0.26	-	
t _{w(STO:STA)}	Stop to Start condition time (bus free)	4.7	-	1.3	-	0.5	-	
t _{SP}	Pulse width of the spikes that are suppressed by the analog filter for standard and fast mode	-	-	0.05	0.09	0.05	0.09	
C _b	Capacitive load for each bus Line	-	400	-	400	-	550 ⁽³⁾	pF

^{1.} Guaranteed based on test during characterization.

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^{2.} When tr(SDA,SCL)<=110 ns.

^{3.} Can be limited. Maximum supported value can be retrieved by referring to the following formulas: $t_{r(SDA/SCL)} = 0.8473 \times R_p \times C_{load} \\ R_{p(min)} = (V_{DD} - V_{OL(max)}) / I_{OL(max)}$

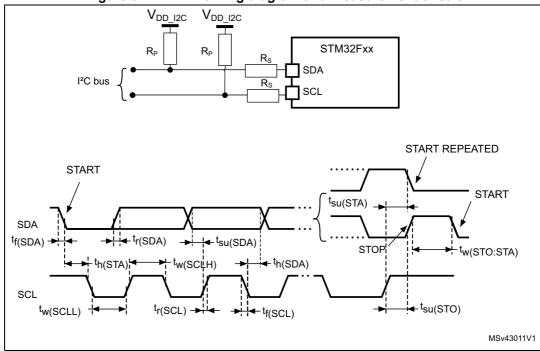


Figure 31. FMPI²C timing diagram and measurement circuit

Note:

ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in Section 6.3.16 does not affect the ADC accuracy.

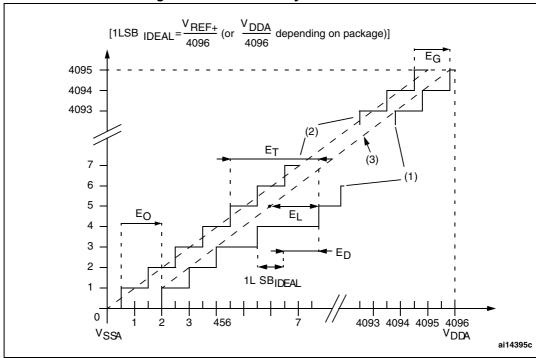


Figure 37. ADC accuracy characteristics

- See also Table 68.
- 2. Example of an actual transfer curve.
- Ideal transfer curve.
- End point correlation line.
- E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves. EO = Offset Error: deviation between the first actual transition and the first ideal one. EG = Gain Error: deviation between the last ideal transition and the last actual one.

 - ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one. EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Table 77. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	Comments
I _{DDA} ⁽⁴⁾	DAC DC VDDA current consumption in quiescent mode ⁽³⁾	-	-	280	380	μA	With no load, middle code (0x800) on the inputs
		-	-	475	625	μA	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
DNL ⁽⁴⁾	Differential non linearity Difference between two consecutive code- 1LSB)	-	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration.
		-	-	-	±2	LSB	Given for the DAC in 12-bit configuration.
INL ⁽⁴⁾	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	-	±1	LSB	Given for the DAC in 10-bit configuration.
		-	-	-	±4	LSB	Given for the DAC in 12-bit configuration.
Offset ⁽⁴⁾	Offset error (difference between measured value at Code (0x800) and the ideal value = V _{REF+} /2)	-	-	-	±10	mV	Given for the DAC in 12-bit configuration
		•	ı	ı	±3	LSB	Given for the DAC in 10-bit at V _{REF+} = 3.6 V
		-	-	-	±12	LSB	Given for the DAC in 12-bit at V _{REF+} = 3.6 V
Gain error ⁽⁴⁾	Gain error	-	-	-	±0.5	%	Given for the DAC in 12-bit configuration
t _{SETŢLING} (Total Harmonic Distortion Buffer ON	-	-	3	6	μs	$C_{LOAD} \le 50 \text{ pF},$ $R_{LOAD} \ge 5 \text{ k}\Omega$
THD ⁽⁴⁾	-	-	-	-	-	dB	$\begin{split} &C_{LOAD} \leq 50 \text{ pF,} \\ &R_{LOAD} \geq 5 \text{ k}\Omega \end{split}$
Update rate ⁽²⁾	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	-	1	MS/ s	$C_{LOAD} \le 50 \text{ pF},$ $R_{LOAD} \ge 5 \text{ k}\Omega$

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7.6 Thermal characteristics

The maximum chip junction temperature (T_Jmax) must never exceed the values given in *Table 15: General operating conditions on page 53*.

The maximum chip-junction temperature, T_J max., in degrees Celsius, may be calculated using the following equation:

 $T_J \max = T_A \max + (PD \max x \Theta_{JA})$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in ° C/W,
- PD max is the sum of P_{INT} max and $P_{I/O}$ max (PD max = P_{INT} max + $P_{I/O}$ max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

P_{I/O} max represents the maximum power dissipation on output pins where:

$$\mathsf{P}_{\mathsf{I/O}} \; \mathsf{max} = \Sigma \; (\mathsf{V}_{\mathsf{OL}} \times \mathsf{I}_{\mathsf{OL}}) + \Sigma ((\mathsf{V}_{\mathsf{DD}} - \mathsf{V}_{\mathsf{OH}}) \times \mathsf{I}_{\mathsf{OH}}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Symbol	Parameter	Value	Unit
	Thermal resistance junction-ambient LQFP48	55	°C/W
	Thermal resistance junction-ambient LQFP64	46	
Θ_{JA}	Thermal resistance junction-ambient UFQFPN48	33	
	Thermal resistance junction-ambient WLCSP36	61	
	Thermal resistance junction-ambient UFBGA64	79	

Table 86. Package thermal characteristics

7.6.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.